

MOCD213-M

DESCRIPTION

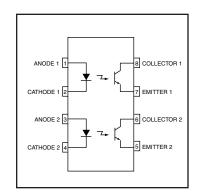
The MOCD213-M device consists of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline plastic package. It is ideally suited for high density applications and eliminates the need for through-the-board mounting.

FEATURES

- U.L. Recognized (File #E90700, Volume 2)
- VDE Recognized (File #136616) (add option "V" for VDE approval, i.e, MOCD213V-M)
- Dual Channel Coupler
- Convenient Plastic SOIC-8 Surface Mountable Package Style
- Minimum Current Transfer Ratio 100% with Input Current of 10 mA
- Minimum BV_{CEO} of 70 Volts Guaranteed
- Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input-Output Isolation of 2500 V_{AC(rms)} Guaranteed

APPLICATIONS

- · Feedback control circuits
- Interfacing and coupling systems of different potentials and impedances
- General purpose switching circuits
- · Monitor and detection circuits



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless otherwise specified)					
Rating	Symbol	Value	Unit		
EMITTER					
Forward Current - Continuous	I _F	60	mA		
Forward Current - Peak (PW = 100 µs, 120 pps)	I _F (pk)	1.0	А		
Reverse Voltage	V _R	6.0	V		
LED Power Dissipation @ T _A = 25°C	В	90	mW		
Derate above 25°C	P_{D}	0.8	mW/°C		
DETECTOR					
Collector-Emitter Voltage	V _{CEO}	70	V		
Emitter-Collector Voltage	V _{ECO}	7.0	V		
Collector Current-Continuous	I _C	150	mA		
Detector Power Dissipation @ T _A = 25°C	ь	150	mW		
Derate above 25°C	P_{D}	1.76	mW/°C		
TOTAL DEVICE					
Input-Output Isolation Voltage ^(1,2,3)	V _{ISO}	2500	Vac(rms)		
(f = 60 Hz, 1 min. Duration)	VISO	2000	vac(IIIIs)		
Total Device Power Dissipation @ $T_A = 25$ °C	P _D	250	mW		
Derate above 25°C		2.94	mW/°C		
Ambient Operating Temperature Range	T _A	-40 to +100	°C		
Storage Temperature Range	T _{stg}	-40 to +125	°C		



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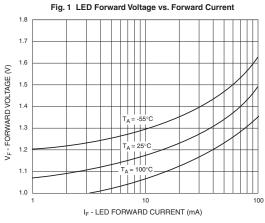
Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
EMITTER		-				
Input Forward Voltage	$I_F = 30 \text{ mA}$	V _F	_	1.25	1.55	V
Reverse Leakage Current	$V_{R} = 6.0 \text{ V}$	I _R	_	0.001	100	μA
Capacitance		С	_	18	_	pF
DETECTOR						
Collector-Emitter Dark Current	$V_{CE} = 10 \text{ V}, T_{A} = 25^{\circ}\text{C}$	I _{CEO1}	_	1.0	50	nA
Collector-Emitter Dark Current	V _{CE} = 10 V, T _A = 100°C	I _{CEO2}	_	1.0	_	μΑ
Collector-Emitter Breakdown Voltage	I _C = 100 μA	BV _{CEO}	70	120	_	V
Emitter-Collector Breakdown Voltage	I _E = 100 μA	BV _{ECO}	7.0	7.8	_	V
Collector-Emitter Capacitance	f = 1.0 MHz, V _{CE} = 0 V	C _{CE}	_	7.0	_	pF
COUPLED						
Output Collector Current ⁽⁴⁾	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	CTR	100	_	_	%
Collector-Emitter Saturation Voltage	$I_C = 2.0 \text{ mA}, I_F = 10 \text{ mA}$	V _{CE (sat)}	_	0.15	0.4	V
Turn-On Time	I_C = 2.0 mA, V_{CC} = 10 V, R_L = 100 Ω (fig 6.)	t _{on}	_	3.0	_	μs
Turn-Off Time	I_C = 2.0 mA, V_{CC} = 10 V, R_L = 100 Ω (fig 6.)	t _{off}	_	2.8	_	μs
Rise Time	I_C = 2.0 mA, V_{CC} = 10 V, R_L = 100 Ω (fig 6.)	t _r	_	1.6	_	μs
Fall Time	I_C = 2.0 mA, V_{CC} = 10 V, R_L = 100 Ω (fig 6.)	t _f	_	2.2	_	μs
Isolation Surge Voltage ^(1,2,3)	f = 60 Hz, t = 1 min.	V _{ISO}	2500	_	_	Vac(rms
Isolation Resistance ⁽²⁾	V _{I-O} = 500 V	R _{ISO}	10 ¹¹	_	_	Ω
Isolation Capacitance ⁽²⁾	$V_{I-O} = 0 \text{ V, f} = 1 \text{ MHz}$	C _{ISO}	_	0.2	_	pF

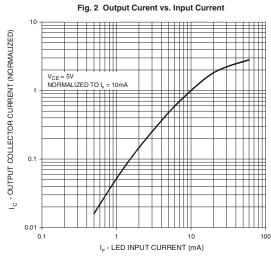
^{**} Typical values at $T_A = 25$ °C

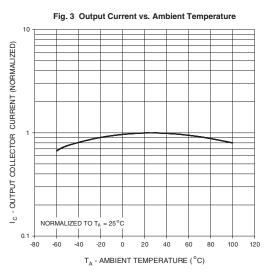
NOTE:

- 1. Input-Output Isolation Voltage, V_{ISO} , is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1, 2, 3 and 4 are common and Pins 5, 6, 7 and 8 are common.
- 3. V_{ISO} rating of 2500 $V_{AC(rms)}$ for t = 1 min. is equivalent to a rating of 3,000 $V_{AC(rms)}$ for t = 1 sec.
- 4. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.









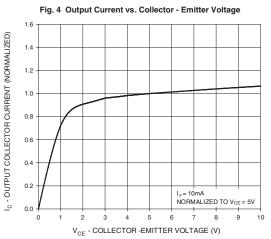
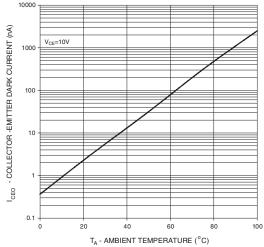


Fig. 5 Dark Current vs. Ambient Temperature





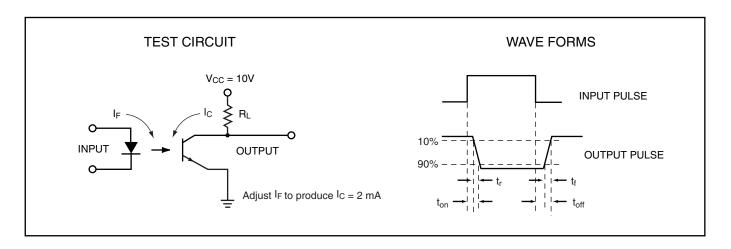
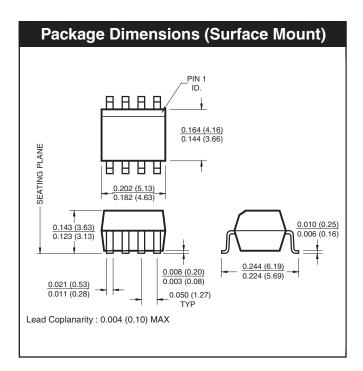
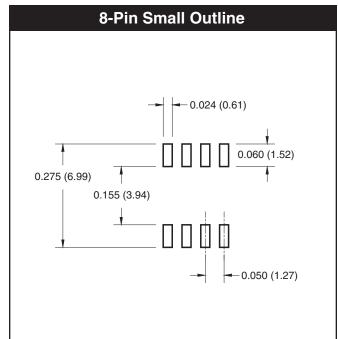


Figure 6. Switching Time Test Circuit and Waveforms







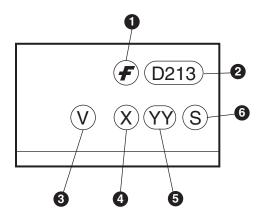


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ORDERING INFORMATION

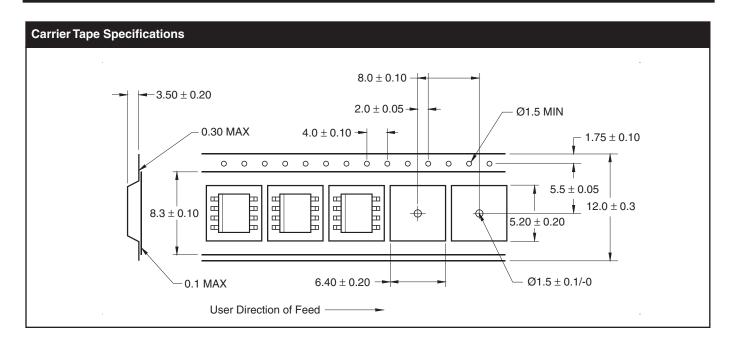
Option	Order Entry Identifier	Description
V	V	VDE 0884
R1	R1	Tape and reel (500 units per reel)
R1V	R1V	VDE 0884, Tape and reel (500 units per reel)
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

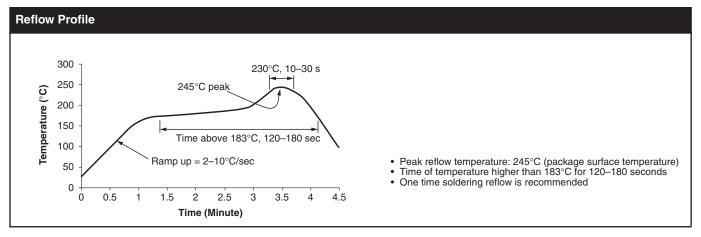
MARKING INFORMATION



Definitions			
1	Fairchild logo		
2	Device number		
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)		
4	One digit year code, e.g., '3'		
5	Two digit work week ranging from '01' to '53'		
6	Assembly package code		









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